

2SC5863

Silicon NPN epitaxial planar type

For general amplification

■ Features

- High collector-emitter voltage (Base open) V_{CEO}
- High transition frequency f_T

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	300	V
Collector-emitter voltage (Base open)	V_{CEO}	300	V
Emitter-base voltage (Collector open)	V_{EBO}	7	V
Collector current	I_C	70	mA
Peak collector current	I_{CP}	100	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

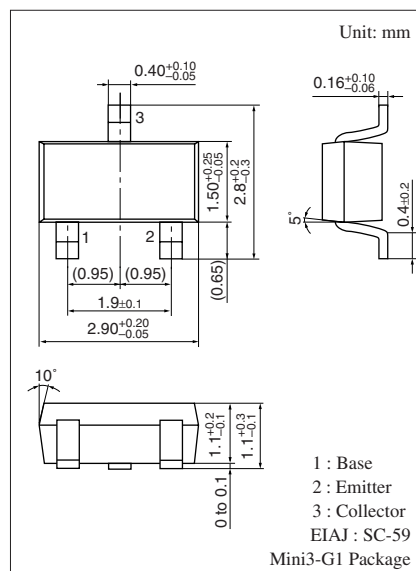
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 100\ \mu\text{A}$, $I_B = 0$	300			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 1\ \mu\text{A}$, $I_C = 0$	7			V
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 120\ \text{V}$, $I_B = 0$			1	μA
Forward current transfer ratio *	h_{FE}	$V_{CE} = 10\ \text{V}$, $I_C = 5\ \text{mA}$	60		220	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50\ \text{mA}$, $I_B = 5\ \text{mA}$			1.2	V
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10\ \text{V}$, $I_E = 0$, $f = 1\ \text{MHz}$			10	pF
Transition frequency	f_T	$V_{CB} = 10\ \text{V}$, $I_E = -10\ \text{mA}$, $f = 200\ \text{MHz}$	50	80		MHz

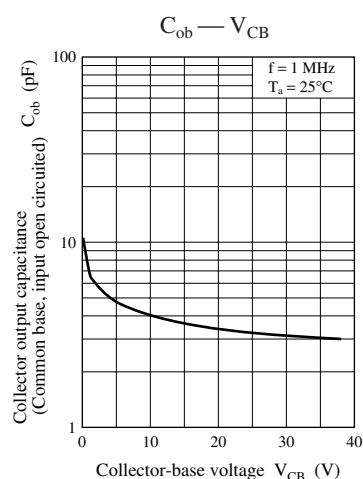
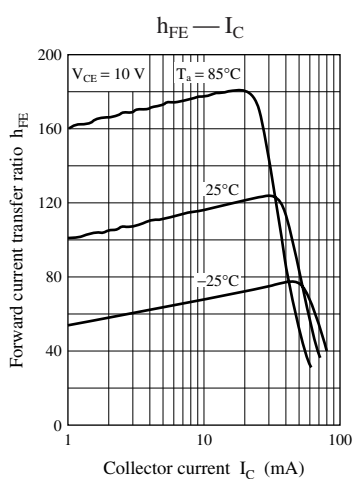
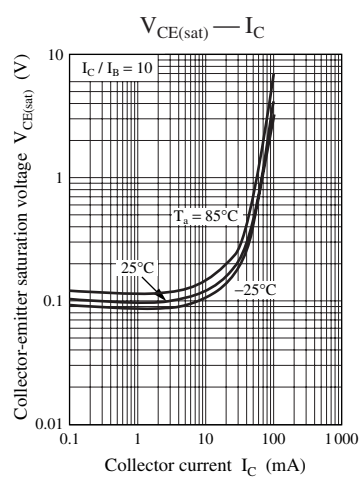
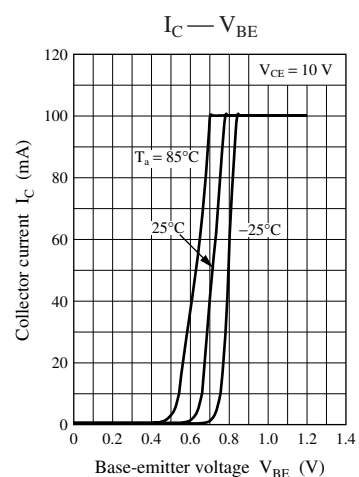
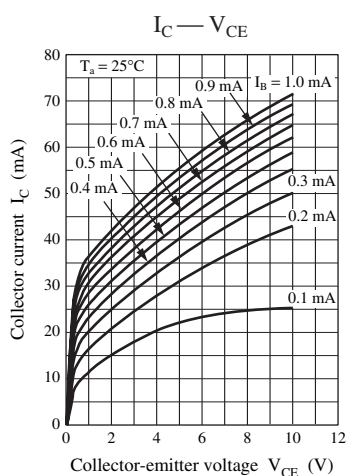
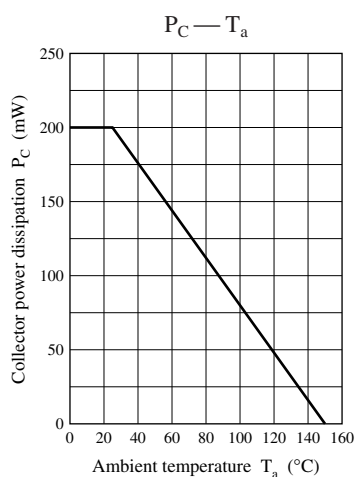
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	Q	R
h_{FE}	60 to 150	100 to 220



Marking Symbol: 7H



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